



PJW4P06A

60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V

Current

-4.0 A

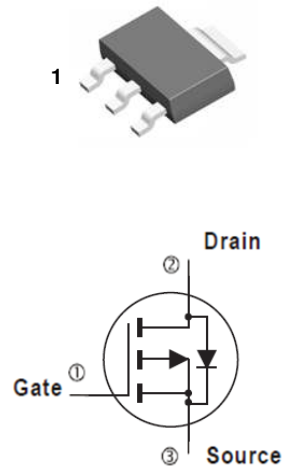
Features

- $R_{DS(ON)}, V_{GS}@-10V, I_D@-4.0A < 110m\Omega$
- $R_{DS(ON)}, V_{GS}@-4.5V, I_D@-2.0 A < 130m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : SOT-223 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.043 ounces, 0.123 grams
- Marking: W4P06A

SOT-223



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_A=25^\circ\text{C}$	-4
		$T_A=70^\circ\text{C}$	-3.2
Pulsed Drain Current ^(Note 1)	I_{DM}	-16	A
Power Dissipation	P_D	$T_A=25^\circ\text{C}$	3.1
		$T_A=70^\circ\text{C}$	2
Single Pulse Avalanche Energy ^(Note 5)	E_{AS}	12.8	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150	$^\circ\text{C}$
Typical Thermal resistance - Junction to Ambient ^(Note 6)	$R_{\theta JA}$	40.3	$^\circ\text{C/W}$

- Limited only By Maximum Junction Temperature



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Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-60	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1.0	-1.7	-2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-4.0A	-	87	110	mΩ
		V _{GS} =-4.5V, I _D =-2.0A	-	110	130	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V	-	-	-1.0	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Dynamic (Note 7)						
Total Gate Charge	Q _g	V _{DS} =-30V, I _D =-4.0A, V _{GS} =-10V (Note 1,2)	-	10	-	nC
Gate-Source Charge	Q _{gs}		-	1.6	-	
Gate-Drain Charge	Q _{gd}		-	3	-	
Input Capacitance	C _{iss}	V _{DS} =-30V, V _{GS} =0V, f=1.0MHZ	-	785	-	pF
Output Capacitance	C _{oss}		-	175	-	
Reverse Transfer Capacitance	C _{rss}		-	112	-	
Turn-On Delay Time	td _(on)	V _{DS} =-30V, RL=30Ω V _{GS} =-10V, R _G =6.2Ω (Note 1,2)	-	8	-	ns
Turn-On Rise Time	t _r		-	15	-	
Turn-Off Delay Time	td _(off)		-	43	-	
Turn-Off Fall Time	t _f		-	8.4	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I _S	---	-	-	-4	A
Diode Forward Voltage	V _{SD}	I _S =-1A, V _{GS} =0V	-	-0.76	-1.0	V

NOTES :

1. Pulse width ≤ 300us, Duty cycle ≤ 2%
2. Essentially independent of operating temperature typical characteristics.
3. The maximum current rating is package limited.
4. Repetitive rating, pulse width limited by junction temperature T_J(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J = 25°C.
5. The test condition is L=0.1mH, I_{AS}=-16A, V_{DD}=-25V, V_{GS}=-10V
6. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
7. Guaranteed by design, not subject to production testing.



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TYPICAL CHARACTERISTIC CURVES

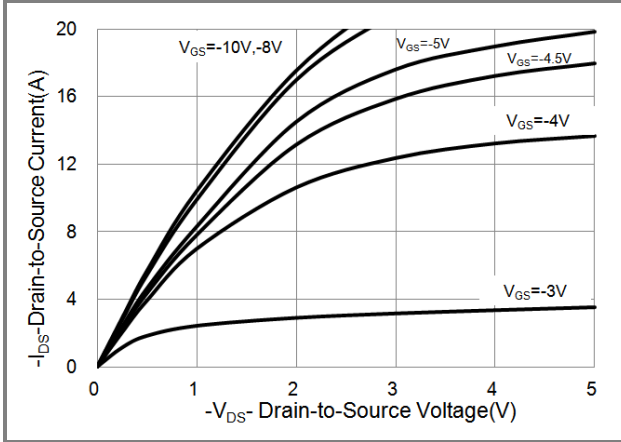


Fig.1 Output Characteristics

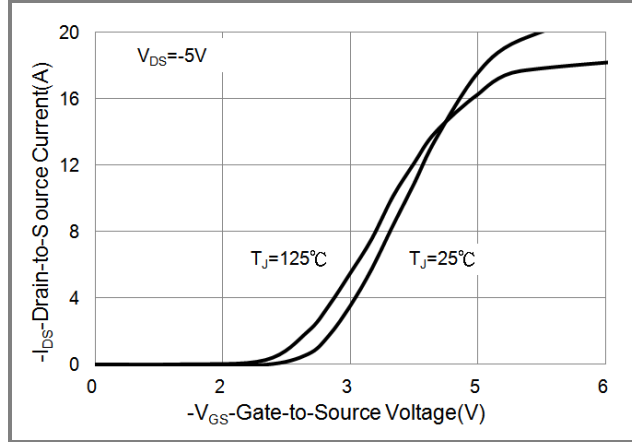


Fig.2 Transfer Characteristics

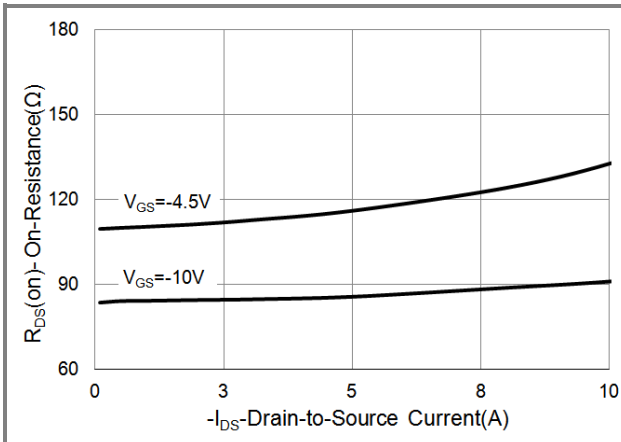


Fig.3 On-Resistance vs. Drain Current

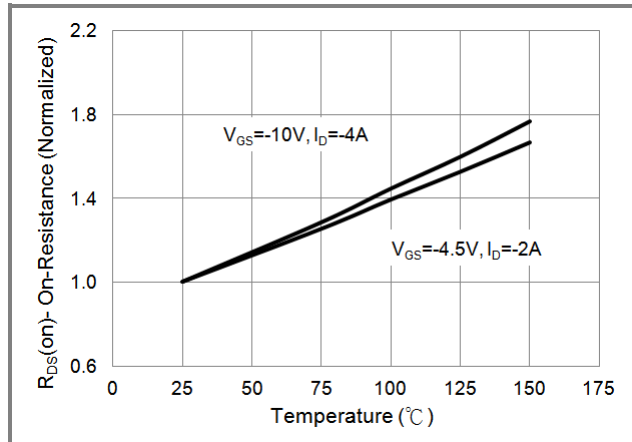


Fig.4 On-Resistance vs. Junction temperature

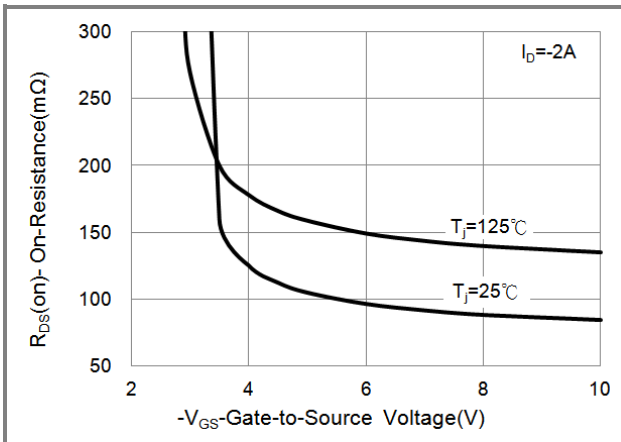


Fig.5 On-Resistance Variation with V_{GS} .

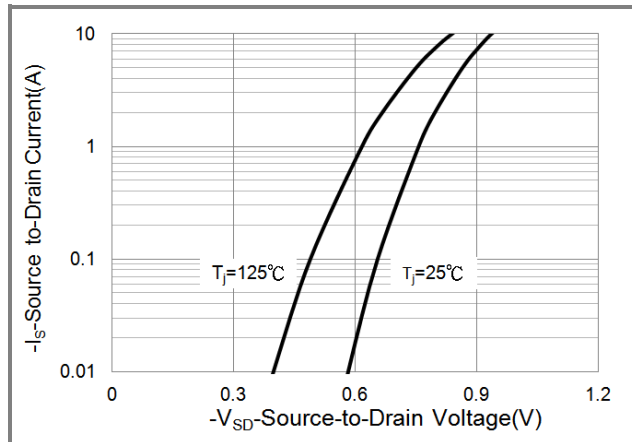


Fig.6 Source-Drain Diode Forward Voltage



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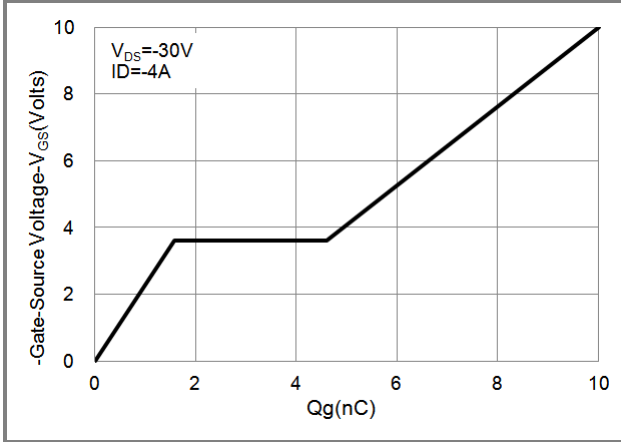


Fig.7 Gate-Charge Characteristics

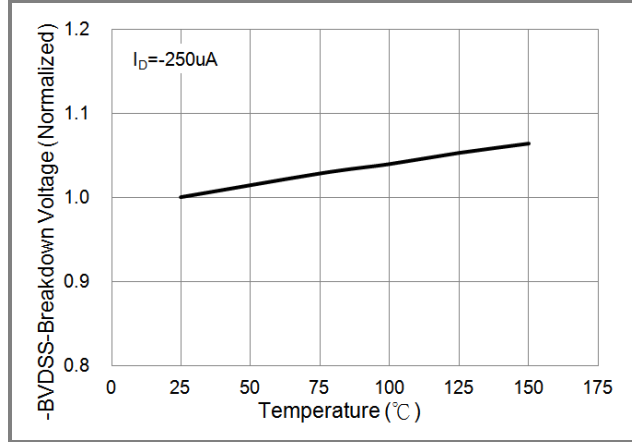


Fig.8 Breakdown Voltage Variation vs. Temperature

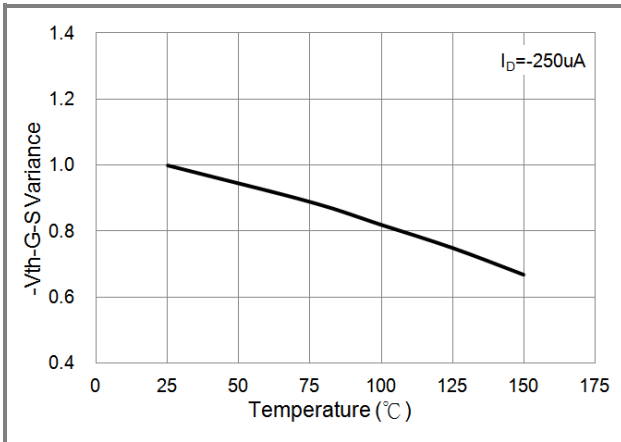


Fig.9 Threshold Voltage Variation with Temperature

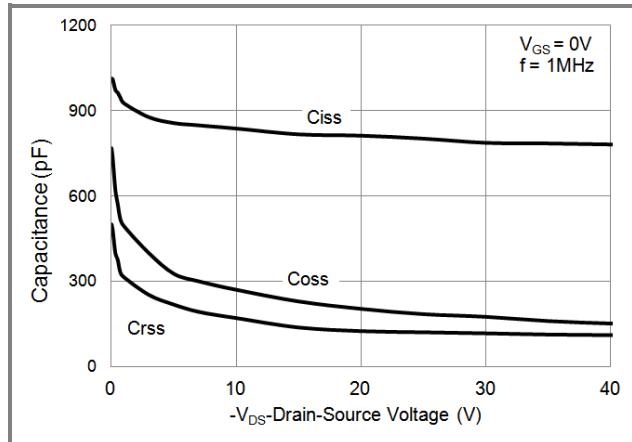


Fig.10 Capacitance vs. Drain-Source Voltage

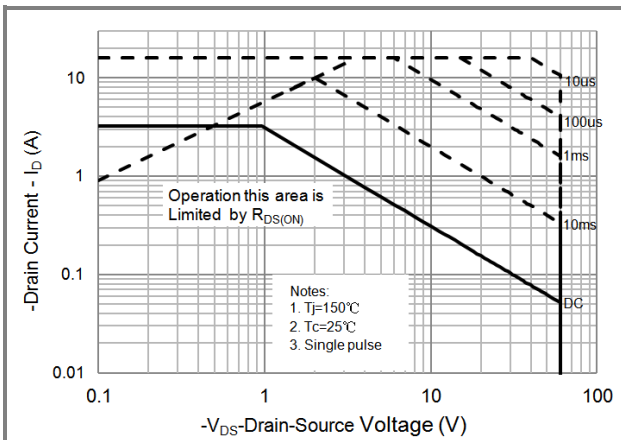


Fig.11 Maximum Safe Operating Area



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TYPICAL CHARACTERISTIC CURVES

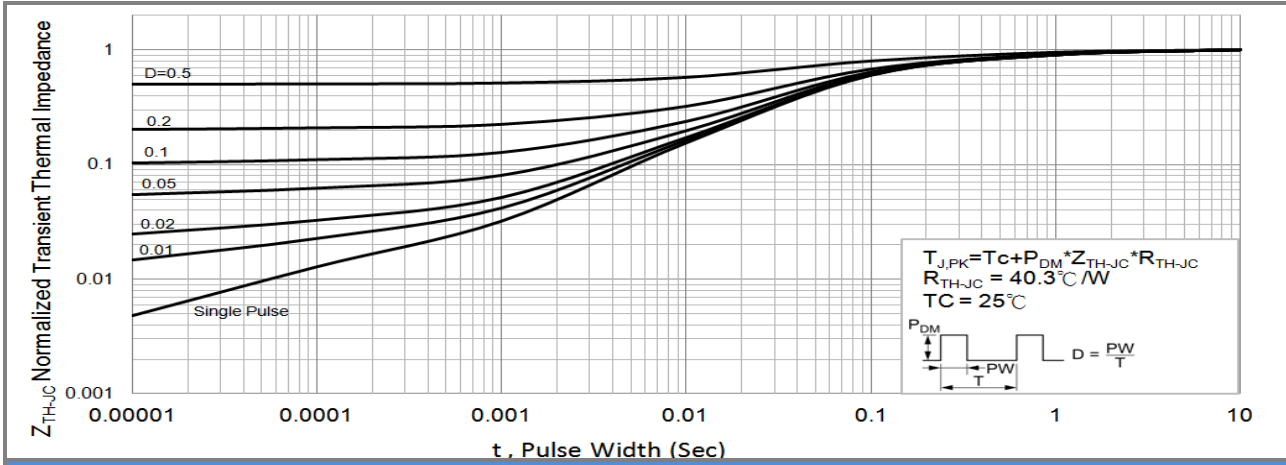
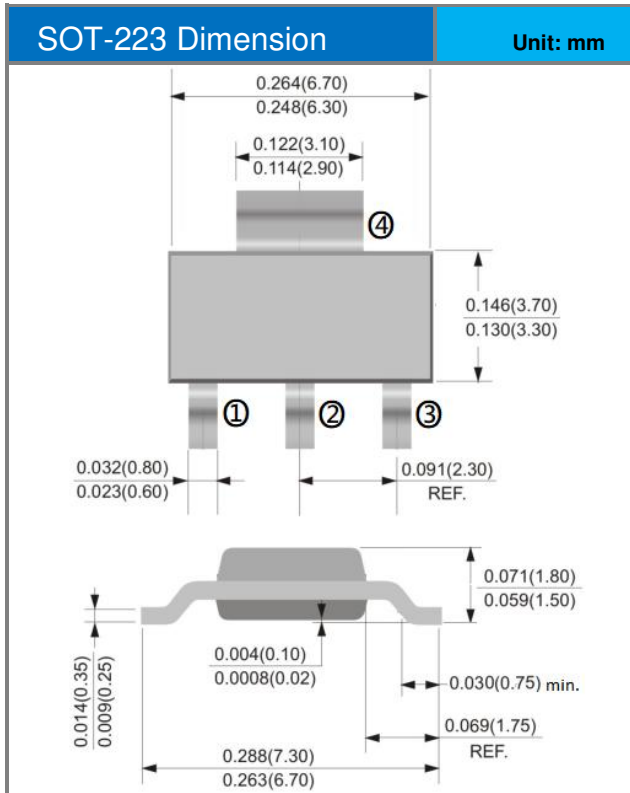


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width



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Packaging Information



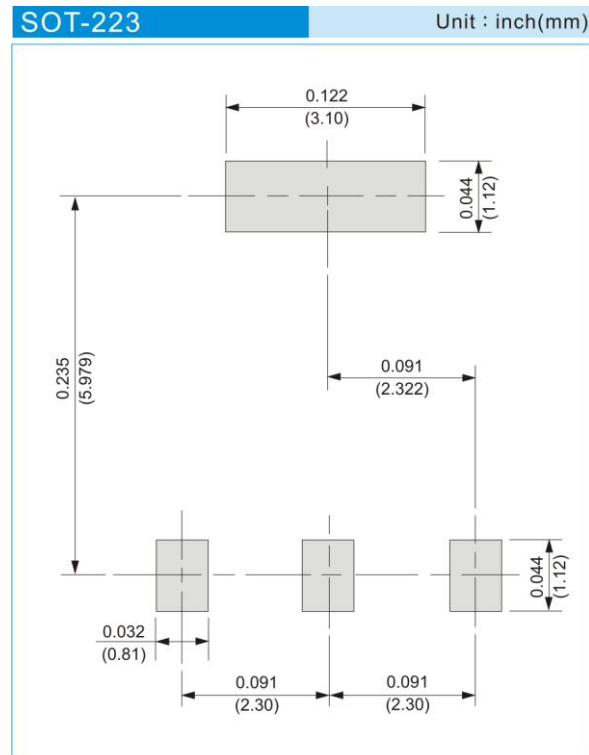


PJW4P06A

PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJW4P06A_R2_00001	SOT-223	2,500pcs / 13" reel	W4P06A	Halogen free

MOUNTING PAD LAYOUT





PJW4P06A

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